

# Saluru B Krupanidhi

## List of Publications by Citations

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419  
papers

9,271  
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47  
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444  
ext. papers

10,062  
ext. citations

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avg, IF

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L-index

| #   | Paper   | IF  | Citations |
|-----|---|-----|-----------|
| 419 | Infrared photodetectors based on reduced graphene oxide and graphene nanoribbons. <i>Advanced Materials</i> , <b>2011</b> , 23, 5419-24   | 24  | 256       |
| 418 | rf planar magnetron sputtering and characterization of ferroelectric Pb(Zr,Ti)O <sub>3</sub> films. <i>Journal of Applied Physics</i> , <b>1983</b> , 54, 6601-6609   | 2.5 | 192       |
| 417 | Biferroic YCrO <sub>3</sub> . <i>Physical Review B</i> , <b>2005</b> , 72,  | 3.3 | 178       |
| 416 | Structural and electrical characteristics of SrTiO <sub>3</sub> thin films for dynamic random access memory applications. <i>Journal of Applied Physics</i> , <b>1993</b> , 73, 7627-7634   | 2.5 | 177       |
| 415 | Electrical transport characteristics of Au/n-GaAs Schottky diodes on n-Ge at low temperatures. <i>Solid-State Electronics</i> , <b>2001</b> , 45, 133-141   | 1.7 | 142       |
| 414 | Current-voltage characteristics of ultrafine-grained ferroelectric Pb(Zr, Ti)O <sub>3</sub> thin films. <i>Journal of Materials Research</i> , <b>1994</b> , 9, 1484-1498   | 2.5 | 141       |
| 413 | Effects of thin oxide in metal/semiconductor and metal/insulator/semiconductor epi-GaAs Schottky diodes. <i>Solid-State Electronics</i> , <b>2000</b> , 44, 1089-1097   | 1.7 | 131       |
| 412 | Switching, fatigue, and retention in ferroelectric Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> thin films. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 1928-1930   | 3.4 | 131       |
| 411 | Excimer laser ablated barium strontium titanate thin films for dynamic random access memory applications. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 1056-1058  | 3.4 | 131       |
| 410 | Enhancement of charge and energy storage in sol-gel derived pure and La-modified PbZrO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 192901   | 3.4 | 116       |
| 409 | Thickness-dependent electrical characteristics of lead zirconate titanate thin films. <i>Journal of Applied Physics</i> , <b>1995</b> , 77, 3981-3986   | 2.5 | 114       |
| 408 | Multi-ion-beam reactive sputter deposition of ferroelectric Pb(Zr,Ti)O <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>1992</b> , 71, 376-388   | 2.5 | 111       |
| 407 | Electrocaloric effect of PMN-PT thin films near morphotropic phase boundary. <i>Bulletin of Materials Science</i> , <b>2009</b> , 32, 259-262   | 1.7 | 109       |
| 406 | Doping dependence of the barrier height and ideality factor of Au/n-GaAs Schottky diodes at low temperatures. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 307, 125-137   | 2.8 | 102       |
| 405 | Structural and electrical studies on rapid thermally processed ferroelectric Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> thin films by metallo-organic solution deposition. <i>Journal of Applied Physics</i> , <b>1992</b> , 72, 5827-5833 | 2.5 | 101       |
| 404 | Structures and electrical properties of barium strontium titanate thin films grown by multi-ion-beam reactive sputtering technique. <i>Journal of Materials Research</i> , <b>1995</b> , 10, 708-726  | 2.5 | 96        |
| 403 | Position and pressure effects in rf magnetron reactive sputter deposition of piezoelectric zinc oxide. <i>Journal of Applied Physics</i> , <b>1984</b> , 56, 3308-3318  | 2.5 | 96        |

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|-----|---|-----|----|
| 402 | Solution processed reduced graphene oxide ultraviolet detector. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 1131-1134  | 2.4 | 92 |
| 401 | Normal ferroelectric to relaxor behavior in laser ablated Ca-doped barium titanate thin films. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 7702   | 2.5 | 90 |
| 400 | Rapid thermal processed thin films of reactively sputtered Ta2O5. <i>Thin Solid Films</i> , <b>1995</b> , 258, 230-235  | 2.2 | 88 |
| 399 | Reactive magnetron co-sputtered antiferroelectric lead zirconate thin films. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 2014-2016   | 3.4 | 87 |
| 398 | Interface states density distribution in Au/n-GaAs Schottky diodes on n-Ge and n-GaAs substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2001</b> , 87, 141-147 | 3.1 | 84 |
| 397 | Pt/Ti/SiO2/Si substrates. <i>Journal of Materials Research</i> , <b>1995</b> , 10, 1508-1515  | 2.5 | 84 |
| 396 | Pulsed excimer laser ablated barium titanate thin films. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 2057-2059   | 3.4 | 78 |
| 395 | Rapid thermally processed ferroelectric Bi4Ti3O12 thin films. <i>Journal of Applied Physics</i> , <b>1992</b> , 72, 5517-5519   | 3.9 | 75 |
| 394 | Effect of heating rate on the crystallization behavior of amorphous PZT thin films. <i>Thin Solid Films</i> , <b>1993</b> , 223, 327-333  | 2.2 | 75 |
| 393 | Band Gap Engineering of Hexagonal SnSe Nanostructured Thin Films for Infra-Red Photodetection. <i>Scientific Reports</i> , <b>2017</b> , 7, 15215   | 4.9 | 74 |
| 392 | Growth and study of antiferroelectric lead zirconate thin films by pulsed laser ablation. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 5862-5869   | 2.5 | 72 |
| 391 | Carbon nanotube-based tandem absorber with tunable spectral selectivity: transition from near-perfect blackbody absorber to solar selective absorber. <i>Advanced Materials</i> , <b>2014</b> , 26, 2552-7              | 2.4 | 71 |
| 390 | Anomalous current transport in Au/low-doped n-GaAs Schottky barrier diodes at low temperatures. <i>Applied Physics A: Materials Science and Processing</i> , <b>1999</b> , 68, 49-55                                    | 2.6 | 67 |
| 389 | Excimer laser ablated lead zirconate titanate thin films. <i>Journal of Applied Physics</i> , <b>1991</b> , 69, 7930-7932   | 2.5 | 66 |
| 388 | Novel Radiation-Induced Properties of Graphene and Related Materials. <i>Macromolecular Chemistry and Physics</i> , <b>2012</b> , 213, 1146-1163  | 2.6 | 63 |
| 387 | Dielectric response in pulsed laser ablated (Ba,Sr)TiO3 thin films. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 849-854   | 2.5 | 62 |
| 386 | Nonlinear electrical properties of lead-lanthanum-titanate thin films deposited by multi-ion-beam reactive sputtering. <i>Journal of Applied Physics</i> , <b>1993</b> , 74, 1949-1959                                  | 2.5 | 62 |
| 385 | Studies on structural and electrical properties of barium strontium titanate thin films developed by metallo-organic decomposition. <i>Thin Solid Films</i> , <b>1997</b> , 305, 144-156                                | 2.2 | 61 |

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|-----|---|-----|----|
| 384 | Effect of neodymium (Nd) doping on the dielectric and ferroelectric characteristics of sol-gel derived lead zirconate titanate (53/47) thin films. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 2975-2984                                  | 2.5 | 60 |
| 383 | Origin of Orientation in Sol-Gel-Derived Lead Titanate Films. <i>Journal of the American Ceramic Society</i> , <b>1993</b> , 76, 1345-1348  | 3.8 | 60 |
| 382 | Study of n-ZnO/p-Si (100) thin film heterojunctions by pulsed laser deposition without buffer layer. <i>Thin Solid Films</i> , <b>2012</b> , 520, 5894-5899   | 2.2 | 59 |
| 381 | Characteristics of field-effect transistors based on undoped and B- and N-doped few-layer graphenes. <i>Solid State Communications</i> , <b>2010</b> , 150, 734-738   | 1.6 | 58 |
| 380 | Unusual photoresponse of indium doped ZnO/organic thin film heterojunction. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 162104  | 3.4 | 56 |
| 379 | Polarization reversal and high dielectric permittivity in lead magnesium niobate titanate thin films. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 1187-1189  | 3.4 | 54 |
| 378 | Electrocaloric effect in antiferroelectric PbZrO <sub>3</sub> thin films. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2008</b> , 2, 230-232  | 2.5 | 52 |
| 377 | Electrical characteristics of excimer laser ablated bismuth titanate films on silicon. <i>Journal of Applied Physics</i> , <b>1992</b> , 72, 3617-3621  | 2.5 | 52 |
| 376 | Excimer laser ablated strontium titanate thin films for dynamic random access memory applications. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 2478-2480   | 3.4 | 50 |
| 375 | Solution Processed Cu <sub>2</sub> CoSnS <sub>4</sub> Thin Films for Photovoltaic Applications. <i>Crystal Growth and Design</i> , <b>2014</b> , 14, 3685-3691  | 3.5 | 49 |
| 374 | Facile synthesis of Cu <sub>2</sub> CoSnS <sub>4</sub> nanoparticles exhibiting red-edge-effect: Application in hybrid photonic devices. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 144312  | 2.5 | 49 |
| 373 | Dielectric relaxation in laser ablated polycrystalline ZrTiO <sub>4</sub> thin films. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 5135  | 2.5 | 49 |
| 372 | Strontium titanate thin films by rapid thermal processing. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 1525-1527   | 3.4 | 47 |
| 371 | Alternating current conduction behavior of excimer laser ablated SrBi <sub>2</sub> Nb <sub>2</sub> O <sub>9</sub> thin films. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 4294  | 2.5 | 46 |
| 370 | Backward switching phenomenon from field forced ferroelectric to antiferroelectric phases in antiferroelectric PbZrO <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 4541-4547                                       | 2.5 | 46 |
| 369 | Study of the electrical properties of pulsed laser ablated (Ba <sub>0.5</sub> Sr <sub>0.5</sub> )TiO <sub>3</sub> thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 57, 135-146 | 3.1 | 46 |
| 368 | Room-temperature gas sensors based on gallium nitride nanoparticles. <i>Solid State Communications</i> , <b>2010</b> , 150, 2053-2056   | 1.6 | 45 |
| 367 | Effect of Li substitution on dielectric and ferroelectric properties of ZnO thin films grown by pulsed-laser ablation. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 034105   | 2.5 | 43 |

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| 366 | Off-centered polarization and ferroelectric phase transition in Li-doped ZnO thin films grown by pulsed-laser ablation. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 104104   | 2.5 | 43 |
| 365 | Dependence of perovskite/pyrochlore phase formation on oxygen stoichiometry in PLT thin films. <i>Journal of Materials Research</i> , <b>1994</b> , 9, 699-711  | 2.5 | 43 |
| 364 | Excimer laser-ablated bismuth titanate thin films. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 781-783   | 3.4 | 42 |
| 363 | Spectroscopic ellipsometry studies on ion beam sputter deposited Pb(Zr, Ti)O <sub>3</sub> films on sapphire and Pt-coated silicon substrates. <i>Thin Solid Films</i> , <b>1993</b> , 230, 15-27  | 2.2 | 41 |
| 362 | Binary group III-nitride based heterostructures: band offsets and transport properties. <i>Journal Physics D: Applied Physics</i> , <b>2015</b> , 48, 423001  | 3   | 40 |
| 361 | Experimental evidence of Ga-vacancy induced room temperature ferromagnetic behavior in GaN films. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 162512   | 3.4 | 40 |
| 360 | Dielectric properties of c-axis oriented Zn <sub>1-x</sub> Mg <sub>x</sub> O thin films grown by multimagnetron sputtering. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 082905   | 3.4 | 40 |
| 359 | Low threshold voltage ZnO thin film transistor with a Zn <sub>0.7</sub> Mg <sub>0.3</sub> O gate dielectric for transparent electronics. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 123717  | 2.5 | 40 |
| 358 | AC properties of laser ablated La-modified lead titanate thin films. <i>Thin Solid Films</i> , <b>2005</b> , 474, 1-9   | 2.2 | 40 |
| 357 | Composition/structure/property relations of multi-ion-beam reactive sputtered lead lanthanum titanate thin films: Part I. Composition and structure analysis. <i>Journal of Materials Research</i> , <b>1992</b> , 7, 3039-3055 <sup>40</sup>                                 | 2.5 | 40 |
| 356 | Enhanced optical absorption of graphene-based heat mirror with tunable spectral selectivity. <i>Solar Energy Materials and Solar Cells</i> , <b>2018</b> , 186, 149-153   | 6.4 | 40 |
| 355 | Solvothermal Synthesis of CuSnS Quantum Dots and Their Application in Near-Infrared Photodetectors. <i>Inorganic Chemistry</i> , <b>2017</b> , 56, 2198-2203  | 5.1 | 39 |
| 354 | Self-Powered, Broad Band, and Ultrafast InGaN-Based Photodetector. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 10418-10425  | 9.5 | 39 |
| 353 | The structural and electrical properties of TiO <sub>2</sub> thin films prepared by thermal oxidation. <i>Physica B: Condensed Matter</i> , <b>2008</b> , 403, 3718-3723  | 2.8 | 39 |
| 352 | Solution processed Cu <sub>2</sub> SnS <sub>3</sub> thin films for visible and infrared photodetector applications. <i>AIP Advances</i> , <b>2016</b> , 6, 025217   | 1.5 | 38 |
| 351 | Solution-based synthesis of cobalt-doped ZnO thin films. <i>Thin Solid Films</i> , <b>2012</b> , 524, 137-143   | 2.2 | 37 |
| 350 | Leakage current behavior in pulsed laser deposited Ba(Zr <sub>0.05</sub> Ti <sub>0.95</sub> )O <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 034106   | 2.5 | 37 |
| 349 | Interface dominated biferroic La <sub>0.6</sub> Sr <sub>0.4</sub> MnO <sub>3</sub> ∩ <sub>0.7</sub> Pb(Mg <sub>1</sub> Nb <sub>2</sub> )O <sub>3</sub> ∩ <sub>0.3</sub> PbTiO <sub>3</sub> epitaxial superlattices. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 122902 | 3.4 | 37 |

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|-----|---|-----|----|
| 348 | Temperature dependent electrical characterisation of Pt/HfO <sub>2</sub> /n-GaN metal-insulator-semiconductor (MIS) Schottky diodes. <i>AIP Advances</i> , <b>2015</b> , 5, 097103  | 1.5 | 36 |
| 347 | Self-annihilation of antiphase boundaries in GaAs epilayers on Ge substrates grown by metal-organic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 5972-5979  | 2.5 | 36 |
| 346 | Facile hydrothermal synthesis and observation of bubbled growth mechanism in nano-ribbons aggregated microspherical Covellite blue-phosphor. <i>Dalton Transactions</i> , <b>2010</b> , 39, 9789-93   | 4.3 | 35 |
| 345 | Large reduction of leakage current by graded-layer La doping in (Ba <sub>0.5</sub> , Sr <sub>0.5</sub> )TiO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 111-113   | 3.4 | 35 |
| 344 | Microstructure related influence on the electrical properties of pulsed laser ablated (Ba, Sr)TiO <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 3506-3513  | 2.5 | 35 |
| 343 | Investigations on magnetron sputtered ZnO thin films and Au/ZnO Schottky diodes. <i>Physica B: Condensed Matter</i> , <b>2007</b> , 391, 344-349  | 2.8 | 33 |
| 342 | Improved ferroelectric and leakage properties in symmetric BiFeO <sub>3</sub> /SrTiO <sub>3</sub> superlattice. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 212902   | 3.4 | 33 |
| 341 | dc and ac transport properties of Mn-doped ZnO thin films grown by pulsed laser ablation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2006</b> , 133, 70-76                                      | 3.1 | 33 |
| 340 | dc leakage behavior in vanadium-doped bismuth titanate thin films. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 094112   | 2.5 | 33 |
| 339 | Effect of acceptor and donor dopants on polarization components of lead zirconate titanate thin films. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 239-241   | 3.4 | 33 |
| 338 | Transport properties of solution processed Cu <sub>2</sub> SnS <sub>3</sub> /AZnO heterostructure for low cost photovoltaics. <i>Solar Energy Materials and Solar Cells</i> , <b>2015</b> , 143, 152-158  | 6.4 | 32 |
| 337 | Dielectric, impedance and ferroelectric characteristics of c-oriented bismuth vanadate films grown by pulsed laser deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2007</b> , 138, 22-30 | 3.1 | 32 |
| 336 | Impedance-fatigue correlated studies on SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> . <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 64, 149-156                                    | 3.1 | 32 |
| 335 | Sputter Synthesis of Ferroelectric Films and Heterostructures. <i>MRS Bulletin</i> , <b>1996</b> , 21, 25-30  | 3.2 | 32 |
| 334 | Electrical properties of strontium titanate thin films by multi-ion-beam reactive sputtering technique. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 1038-1040  | 3.4 | 32 |
| 333 | Study of electrical properties of pulsed excimer laser deposited strontium titanate films. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 2604-2611  | 2.5 | 32 |
| 332 | Near infrared detectors based on HgSe and HgCdSe quantum dots generated at the liquid-liquid interface. <i>Journal of Materials Chemistry C</i> , <b>2013</b> , 1, 6184   | 7.1 | 31 |
| 331 | Semipolar and nonpolar GaN epi-films grown on m-sapphire by plasma assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 204502   | 2.5 | 31 |

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| 330 | Dielectric response and impedance spectroscopy of 0.7Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> -0.3PbTiO <sub>3</sub> thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2003</b> , 98, 204-212                     | 3.1 | 31 |
| 329 | Enhanced electrical properties of ferroelectric Pb(Zr <sub>0.5</sub> , Ti <sub>0.5</sub> )O <sub>3</sub> thin films grown with low-energy oxygen ion assistance. <i>Journal of Applied Physics</i> , <b>1993</b> , 74, 3373-3382   | 2.5 | 31 |
| 328 | Pulsed excimer laser deposition and characterization of ferroelectric Pb(Zr <sub>0.52</sub> Ti <sub>0.48</sub> )O <sub>3</sub> thin films. <i>Journal of Materials Research</i> , <b>1992</b> , 7, 2521-2529   | 2.5 | 31 |
| 327 | Development of ferroelectric Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> thin films by metallo-organic decomposition process and rapid thermal annealing. <i>Integrated Ferroelectrics</i> , <b>1992</b> , 1, 111-127   | 0.8 | 31 |
| 326 | Wafer-scale synthesis of a uniform film of few-layer MoS <sub>2</sub> on GaN for 2D heterojunction ultraviolet photodetector. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 374003   | 3   | 30 |
| 325 | Si incorporation and Burstein-Moss shift in n-type GaAs. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 60, 1-11  | 3.1 | 30 |
| 324 | Pulsed excimer laser ablation of (Pb,La)TiO <sub>3</sub> thin films for dynamic random access memory devices. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 1591-1593   | 3.4 | 30 |
| 323 | Zn incorporation and band gap shrinkage in p-type GaAs. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 4931-4937  | 2.5 | 29 |
| 322 | Interfacial coupling and its size dependence in PbTiO <sub>3</sub> and PbMg <sub>1/3</sub> Nb <sub>2/3</sub> O <sub>3</sub> multilayers. <i>Physical Review B</i> , <b>2006</b> , 74,  | 3.3 | 29 |
| 321 | Impact of microstructure on the electrical stress induced effects of pulsed laser ablated (Ba, Sr)TiO <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 3056-3062   | 2.5 | 29 |
| 320 | Growth and characterization of SrBi <sub>2</sub> Nb <sub>2</sub> O <sub>9</sub> thin films by pulsed-laser ablation. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 2656-2658  | 3.4 | 29 |
| 319 | Transport properties of CuIn <sub>(1-x)</sub> Al <sub>(x)</sub> Se <sub>2</sub> /AZnO heterostructure for low cost thin film photovoltaics. <i>Dalton Transactions</i> , <b>2014</b> , 43, 1974-83   | 4.3 | 28 |
| 318 | Ac conductivity studies on the Li irradiated PZT and SBT ferroelectric thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2003</b> , 100, 93-101   | 3.1 | 28 |
| 317 | Role of La <sub>0.5</sub> Sr <sub>0.5</sub> CoO <sub>3</sub> template layers on dielectric and electrical properties of pulsed-laser ablated Pb(Nb <sub>2/3</sub> Mg <sub>1/3</sub> )O <sub>3</sub> -PbTiO <sub>3</sub> thin films. <i>Thin Solid Films</i> , <b>2003</b> , 424, 274-282 | 2.2 | 28 |
| 316 | Preparation and properties of thermally evaporated lead germanate films. <i>Journal of Applied Physics</i> , <b>1980</b> , 51, 5408  | 2.5 | 28 |
| 315 | Cobalt-doped ZnO nanowires on quartz: Synthesis by simple chemical method and characterization. <i>Journal of Crystal Growth</i> , <b>2012</b> , 343, 7-12   | 1.6 | 27 |
| 314 | Dielectric properties of (110) oriented PbZrO <sub>3</sub> and La-modified PbZrO <sub>3</sub> thin films grown by sol-gel process on Pt(111)-SiO <sub>2</sub> /Si substrate. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 044102   | 2.5 | 27 |
| 313 | Analysis of leakage current conduction phenomenon in thin SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> films grown by excimer laser ablation. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 4543-4548  | 2.5 | 27 |

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| 312 | ac transport studies of La-modified antiferroelectric lead zirconate thin films. <i>Physical Review B</i> , <b>2002</b> , 65,  | 3.3 | 27 |
| 311 | Defect and strain modulated highly efficient ZnO UV detector: Temperature and low-pressure dependent studies. <i>Applied Surface Science</i> , <b>2020</b> , 505, 144365   | 6.7 | 27 |
| 310 | Enhanced UV detection by non-polar epitaxial GaN films. <i>AIP Advances</i> , <b>2015</b> , 5, 127208  | 1.5 | 26 |
| 309 | Near-infrared photoactive Cu <sub>2</sub> ZnSnS <sub>4</sub> thin films by co-sputtering. <i>AIP Advances</i> , <b>2013</b> , 3, 082132  | 1.5 | 26 |
| 308 | Dielectric relaxation in antiferroelectric multigrain PbZrO <sub>3</sub> thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 78, 75-83   | 3.1 | 26 |
| 307 | Property modification of ferroelectric Pb(Zr,Ti)O <sub>3</sub> thin films by low-energy oxygen ion bombardment during film growth. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 1246-1248  | 3.4 | 26 |
| 306 | Recent advances in physical vapor growth processes for ferroelectric thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1992</b> , 10, 1569-1577   | 2.9 | 26 |
| 305 | Growth of ferroelectric Li-doped ZnO thin films for metal-ferroelectric-semiconductor FET. <i>Journal Physics D: Applied Physics</i> , <b>2006</b> , 39, 2664-2669   | 3   | 25 |
| 304 | Improved growth of GaN layers on ultra thin silicon nitride/Si (111) by RF-MBE. <i>Materials Research Bulletin</i> , <b>2010</b> , 45, 1581-1585   | 5.1 | 24 |
| 303 | Fabrication of TiNb <sub>2</sub> O <sub>7</sub> thin film electrodes for Li-ion micro-batteries by pulsed laser deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2016</b> , 213, 90-97 | 3.1 | 23 |
| 302 | Synthesis and structural characterization of Ba <sub>0.6</sub> Sr <sub>0.4</sub> TiO <sub>3</sub> nanotubes. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , <b>2007</b> , 367, 356-359                             | 2.3 | 23 |
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| 187 | Surface spin glass behavior in sol-gel derived La <sub>0.7</sub> Ca <sub>0.3</sub> MnO <sub>3</sub> nanotubes. <i>Dalton Transactions</i> , <b>2008</b> , 4708-10  | 4.3 | 10 |

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| 183 | Temperature-Dependent Electrical Transport and Optoelectronic Properties of $\text{SnS}_2/\text{p-Si}$ Heterojunction. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 2155-2163  | 4   | 10 |
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| 167 | Reduced graphene oxide-based broad band photodetector and temperature sensor: effect of gas adsorption on optoelectrical properties. <i>Journal of Nanoparticle Research</i> , <b>2018</b> , 20, 1   | 2.3 | 9 |
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| 164 | Mechanistic view on efficient photodetection by solvothermally reduced graphene oxide. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2017</b> , 28, 14818-14826   | 2.1 | 8 |
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| 161 | Effect of N/Ga flux ratio on transport behavior of Pt/GaN Schottky diodes. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 064502   | 2.5 | 8 |
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| 158 | Investigation of true remnant polarization response in heterostructured artificial biferroics. <i>Solid State Communications</i> , <b>2010</b> , 150, 660-662  | 1.6 | 8 |
| 157 | Electron cyclotron resonance plasma assisted sputter deposition of boron nitride films. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 628-630   | 3.4 | 8 |
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| 152 | Enhanced humidity responsive ultrasonically nebulised V <sub>2</sub> O <sub>5</sub> thin films. <i>Nano Express</i> , <b>2020</b> , 1, 010005  | 2   | 8 |
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| 110 | Role of template layer on microstructure, phase formation and polarization behavior of ferroelectric relaxor thin films. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 104111  | 2.5  | 5 |
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| 98  | Different types of band alignment at MoS <sub>2</sub> /(Al, Ga, In)N heterointerfaces. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 252102   | 3.4  | 4 |
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| 79 | Effect of electric field on dielectric response of PMNBT thin films <b>2004</b> , 113, 190-190   |     | 4 |

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| 78 | Note: Simultaneous water quality monitoring and degradation of hazardous organic pollutants. <i>Review of Scientific Instruments</i> , <b>2018</b> , 89, 096102   | 1.7 | 4 |
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| 75 | Electrocaloric Effect in 0.85PMN-0.15PT Thin Films Deposited by Pulsed Laser Deposition. <i>Ferroelectrics</i> , <b>2013</b> , 453, 38-43   | 0.6 | 3 |
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